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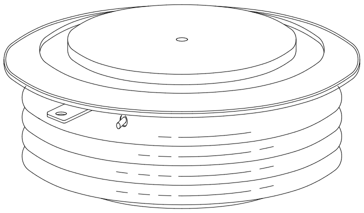
T11C



Device Type	V_{RRM} (1)	V_{DRM} (1)	V_{RSM} (1)
KP2600/12	1200	1200	1400
KP2600/14	1400	1400	1600
KP2600/16	1600	1600	1760
KP2600/18	1800	1800	1900

V_{RRM} = Repetitive peak reverse voltage
V_{DRM} = Repetitive peak off state voltage
V_{RSM} = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage and off state leakage	I_{RRM}/I_{DRM}	5 mA 150 mA (3)
Critical rate of voltage rise	dv/dt (4)	1000 V/ s

Notes:
(1) All voltage ratings are specified for an applied 50Hz sinusoidal waveform over the temperature range -40 ºC to +125 ºC.
(2) 10 msec. max. pulse width
(3) Maximum value for Tj = 125 ºC.
(4) Minimum value for linear and exponential waveshape to 67% rated V_{DRM}. Gate open. Tj = 125 ºC.
(5).The value of di/dt is established in accordance with EIA/NIMA Standard JB/T 8950.2-2013

Peak gate power dissipation	P_G